

**ESD protected N-Channel Enhancement Mode MOSFET**

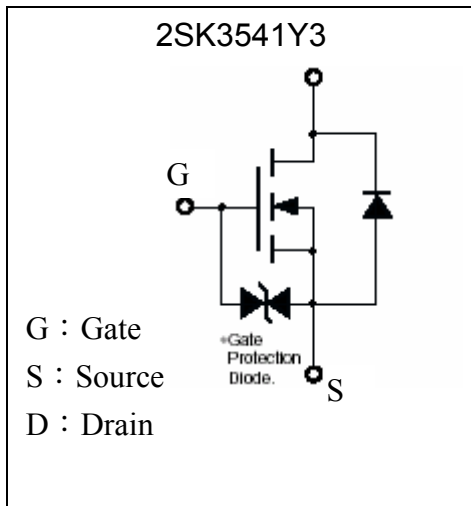
# 2SK3541Y3

BV <sub>DSS</sub>	30V
I <sub>D</sub>	100mA
R <sub>DS(on)@4V</sub>	3.4Ω (TYP)
R <sub>DS(on)@2.5V</sub>	6.9Ω (TYP)

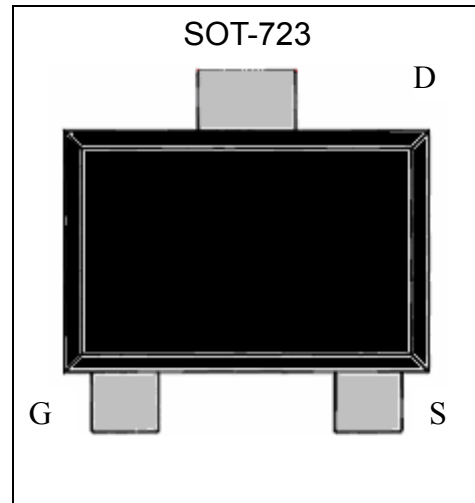
**Description**

- Low voltage drive(2.5V drive) makes this device ideal for portable equipment.
- High speed switching
- ESD protected device
- Pb-free lead plating & halogen-free package

**Symbol**



**Outline**



**Absolute Maximum Ratings (Ta=25°C)**

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		BV <sub>DSS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current	Continuous	I <sub>D</sub>	±100	mA
	Pulsed	I <sub>DP</sub>	±200 *1	mA
Reverse Drain Current	Continuous	I <sub>DR</sub>	±100	mA
	Pulsed	I <sub>DRP</sub>	±200 *1	mA
Total Power Dissipation		P <sub>D</sub>	150 *2	mW
ESD susceptibility			750 *3	V
Operating Junction and Storage Temperature Range		T <sub>j</sub> ; T <sub>stg</sub>	-55~+150	°C
Thermal Resistance, Junction-to-Ambient		R <sub>th,ja</sub>	833	°C/W

Note : \*1. Pulse Width ≤ 10μs, Duty cycle ≤ 1%  
 \*2. With each pin mounted on the recommended lands.  
 \*3. Human body model, 1.5kΩ in series with 100pF



**Electrical Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> =0, I <sub>D</sub> =100μA
V <sub>GS(th)</sub>	0.8	1.3	1.5	V	V <sub>DS</sub> =3V, I <sub>D</sub> =100μA
I <sub>GSS</sub>	-	-	±1	μA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0
I <sub>DSS</sub>	-	-	100	nA	V <sub>DS</sub> =30V, V <sub>GS</sub> =0
R <sub>DSON</sub>	-	3.4	8	Ω	V <sub>GS</sub> =4V, I <sub>D</sub> =10mA
	-	6.9	13		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1mA
GFS	20	50	-	mS	V <sub>DS</sub> =3V, I <sub>D</sub> =10mA
<b>Dynamic</b>					
C <sub>iss</sub>	-	12.5	-	pF	V <sub>DS</sub> =5V, V <sub>GS</sub> =0, f=1MHz
C <sub>oss</sub>	-	7.3	-		
C <sub>rss</sub>	-	3.5	-		
t <sub>d(on)</sub>	-	15	-	ns	V <sub>DD</sub> ≐ 5V, I <sub>D</sub> =10mA, V <sub>GS</sub> =5V, R <sub>L</sub> =500Ω, R <sub>G</sub> =10Ω
t <sub>r</sub>	-	35	-		
t <sub>d(off)</sub>	-	75	-		
t <sub>f</sub>	-	75	-		
<b>Source-Drain Diode</b>					
*V <sub>SD</sub>	-	0.88	1.2	V	V <sub>GS</sub> =0V, I <sub>S</sub> =100mA

\*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

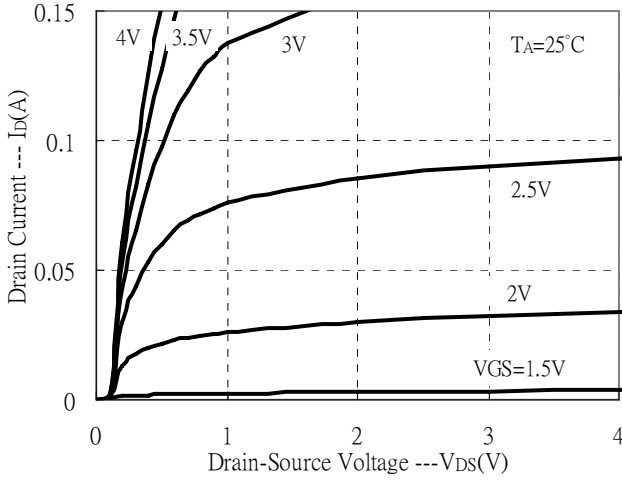
**Ordering Information**

Device	Package	Shipping	Marking
2SK3541Y3	SOT-723 (Pb-free lead plating & halogen-free package)	8000 pcs / Tape & Reel	KN

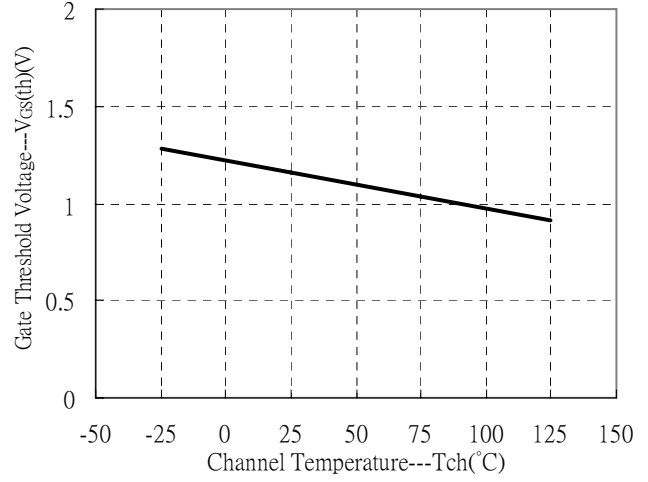


Typical Characteristics

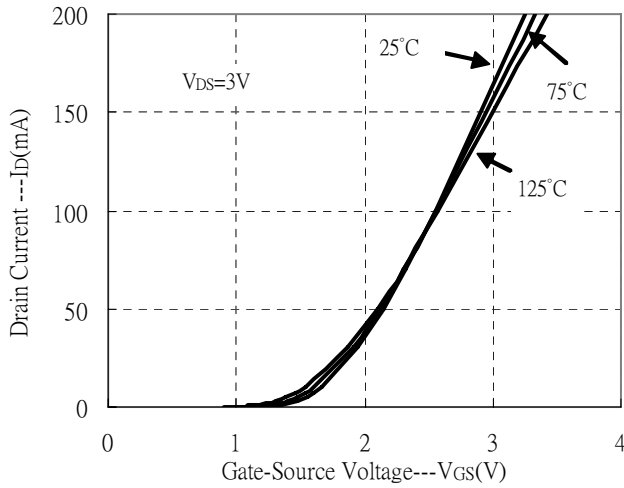
Typical Output Characteristics



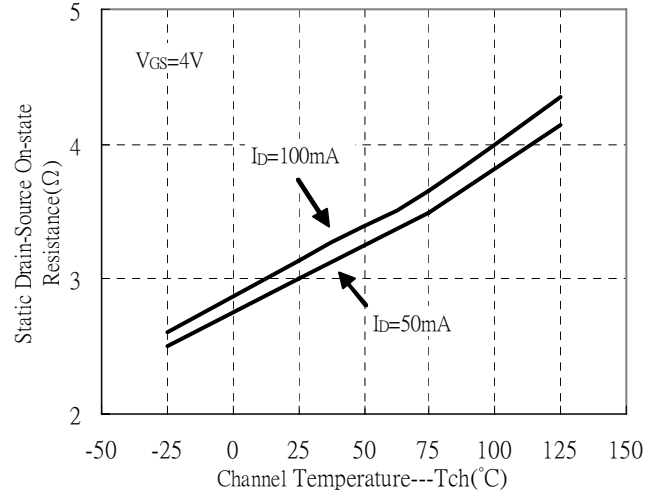
Gate Threshold Voltage vs Channel Temperature



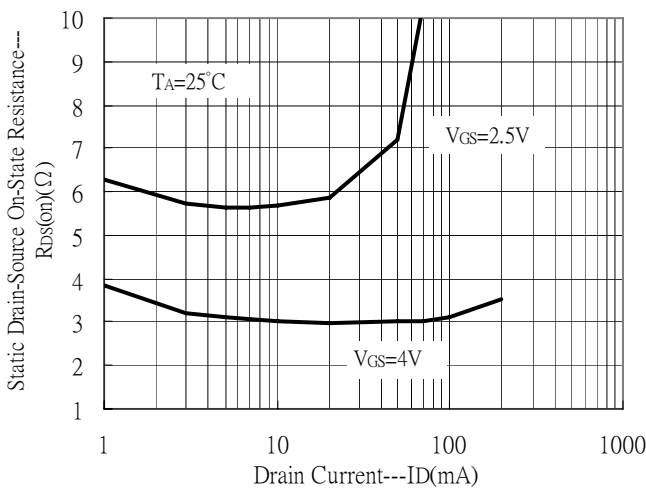
Typical Transfer Characteristics



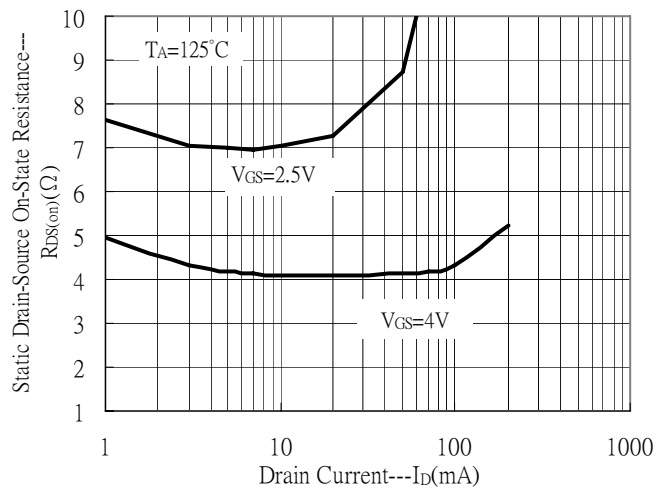
Static Drain-Source On-state Resistance with Temperature



Static Drain-Source On-State resistance vs Drain Current

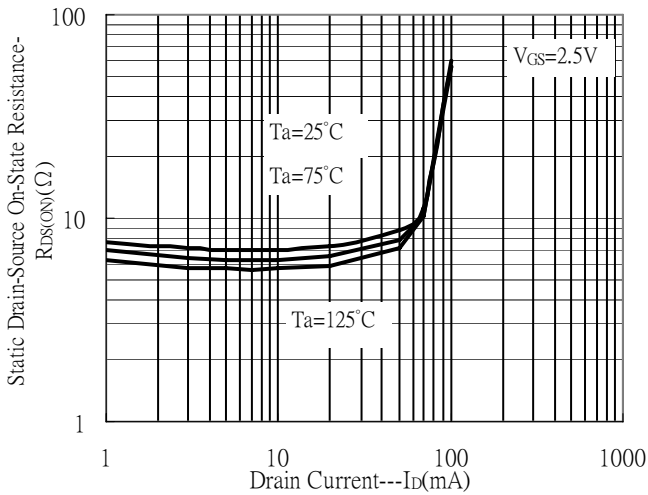


Static Drain-Source On-State resistance vs Drain Current

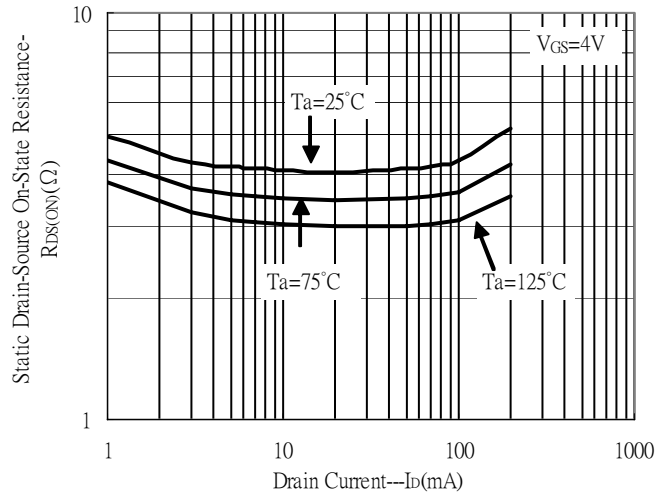


**Typical Characteristics(Cont.)**

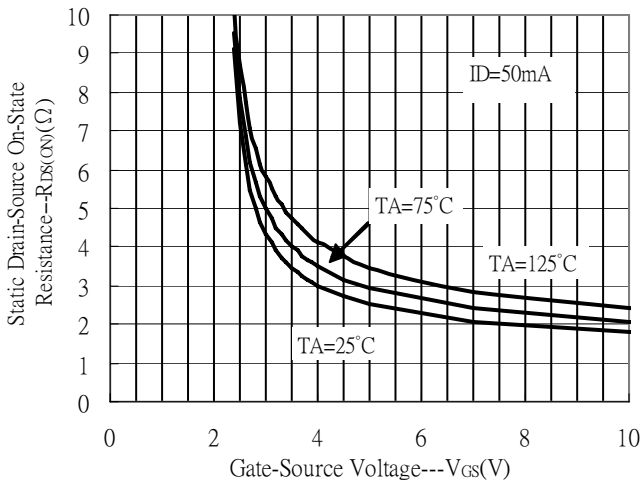
Static Drain-Source On-State Resistance vs Drain Current



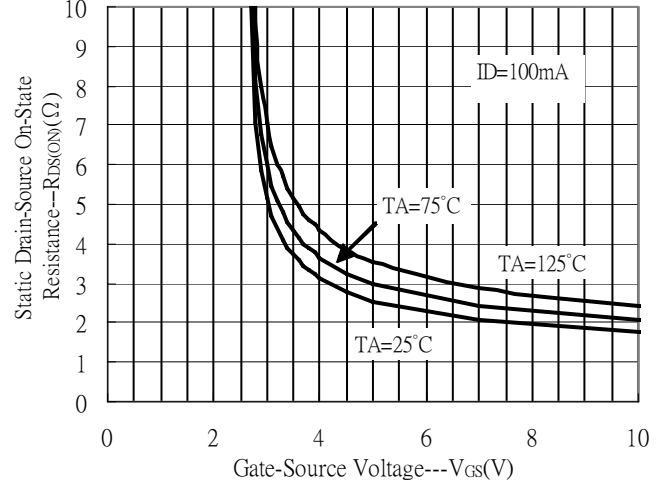
Static Drain-Source On-State Resistance vs Drain Current



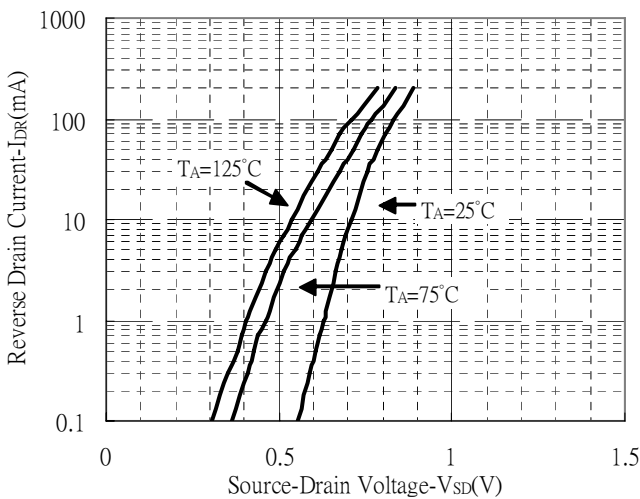
Static Drain-Source On-State Resistance vs Gate-Source Voltage



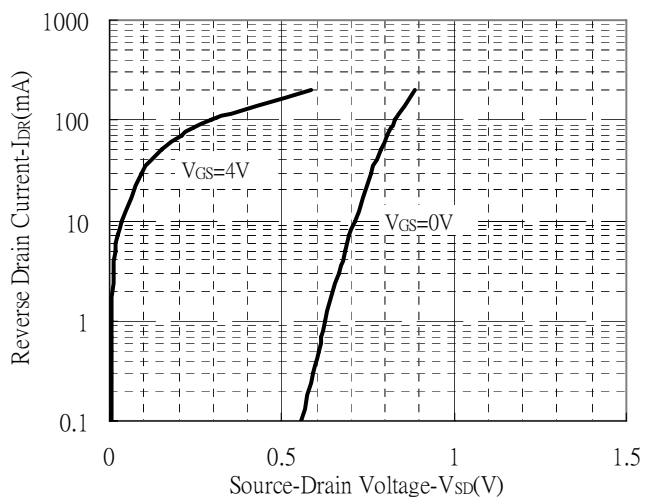
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Reverse Drain Current vs Source-Drain Voltage(I)

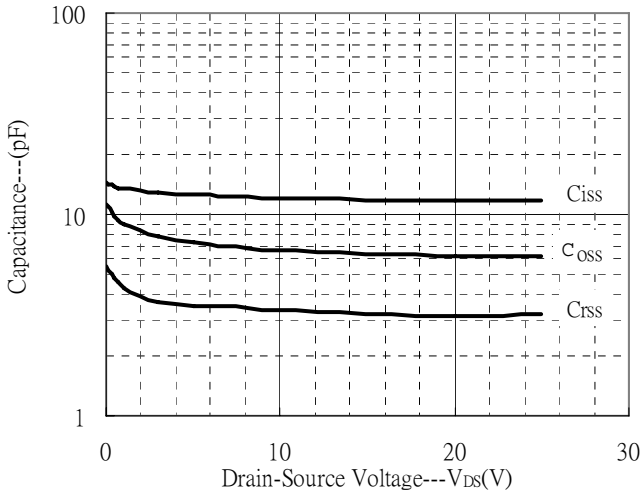


Reverse Drain Current vs Source-Drain Voltage(II)

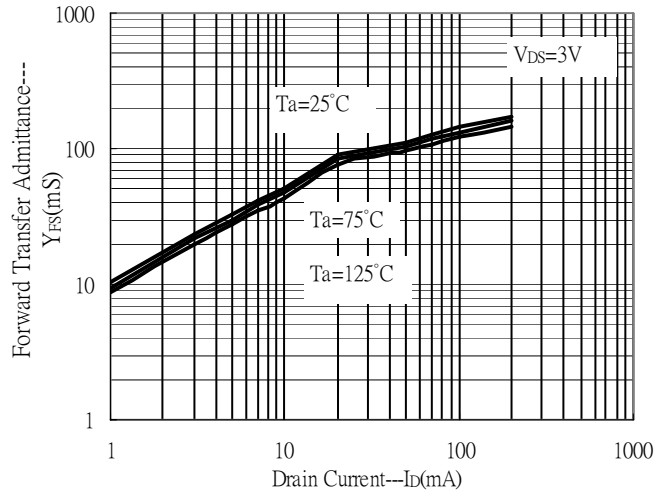


**Typical Characteristics(Cont.)**

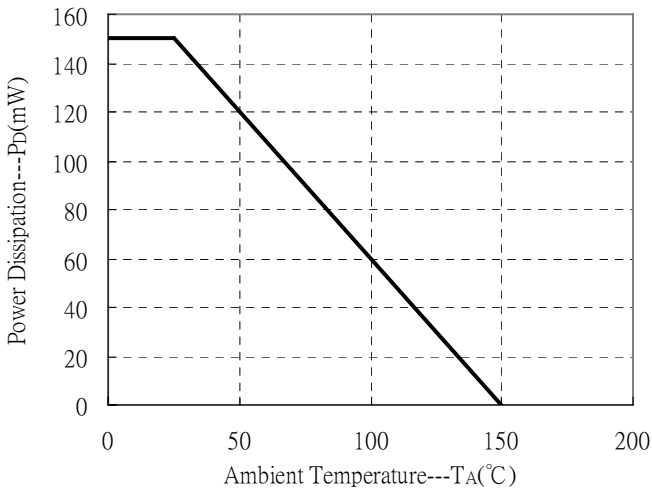
Capacitance vs Drain-to-Source Voltage



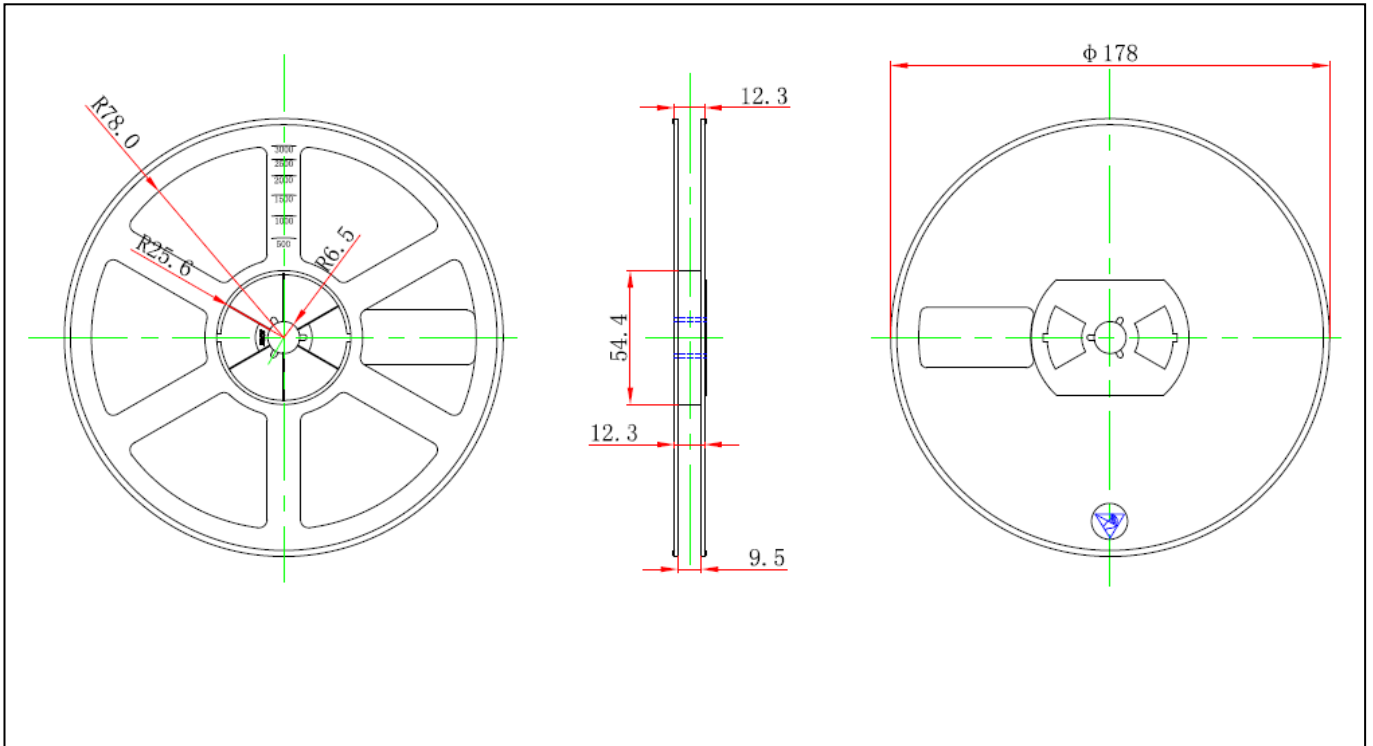
Forward Transfer Admittance vs Drain Current



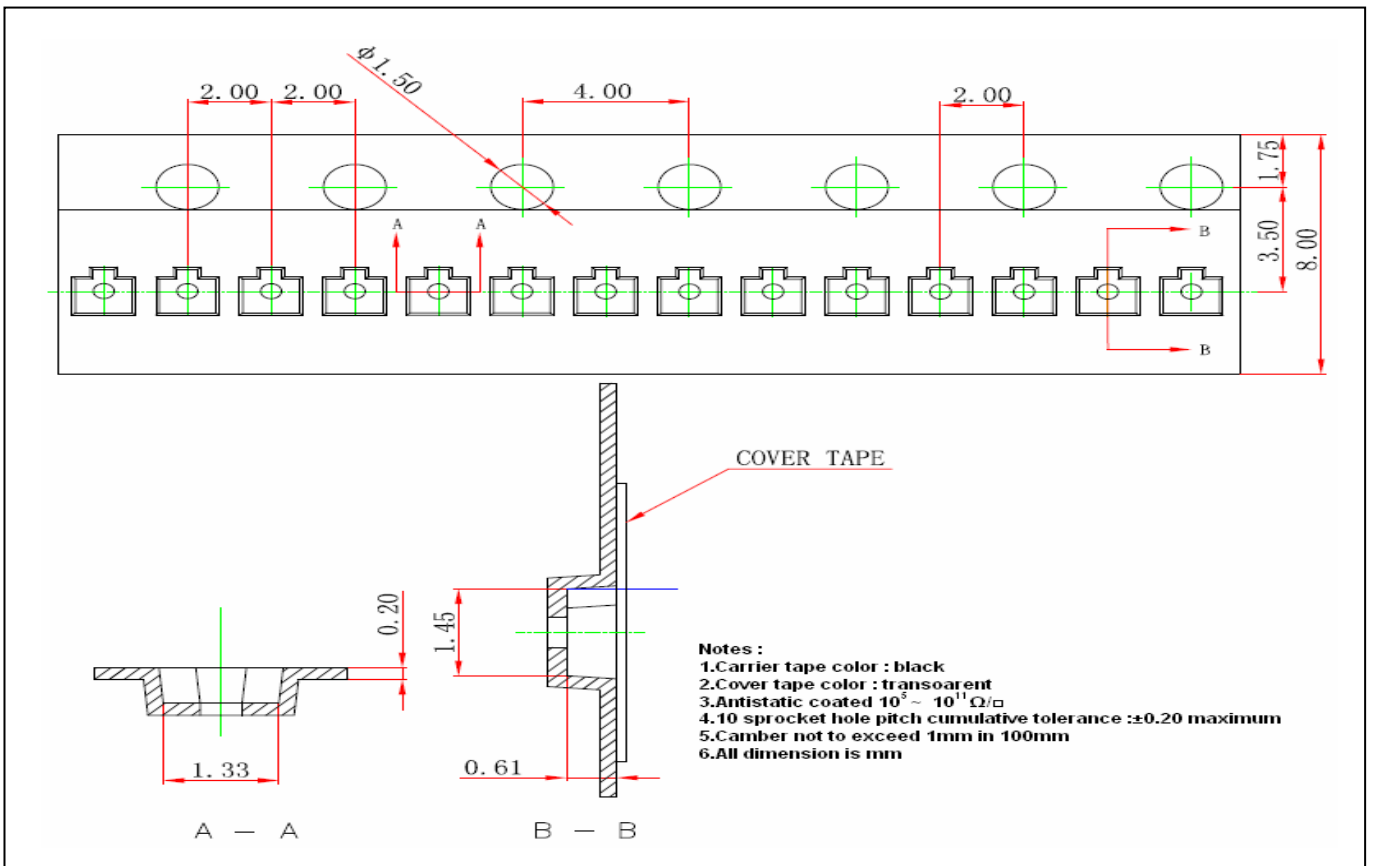
Power Derating Curve



**Reel Dimension**



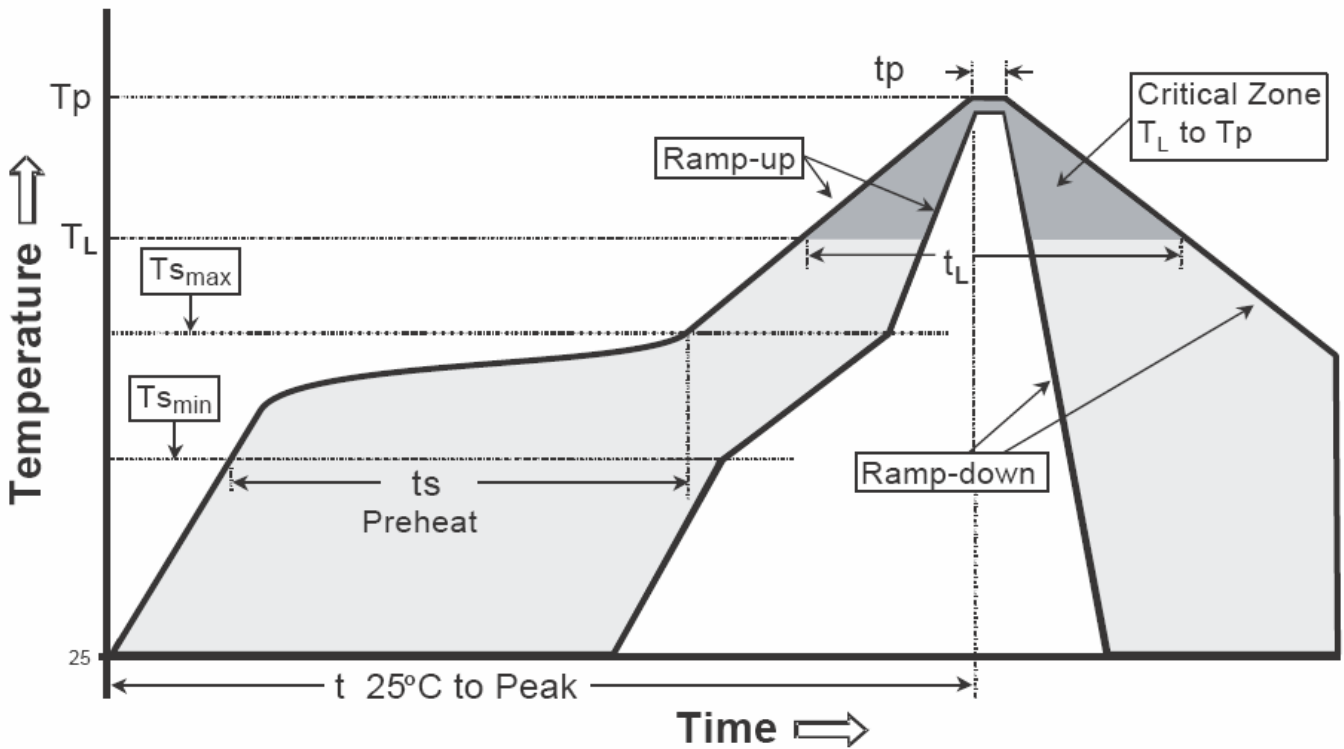
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

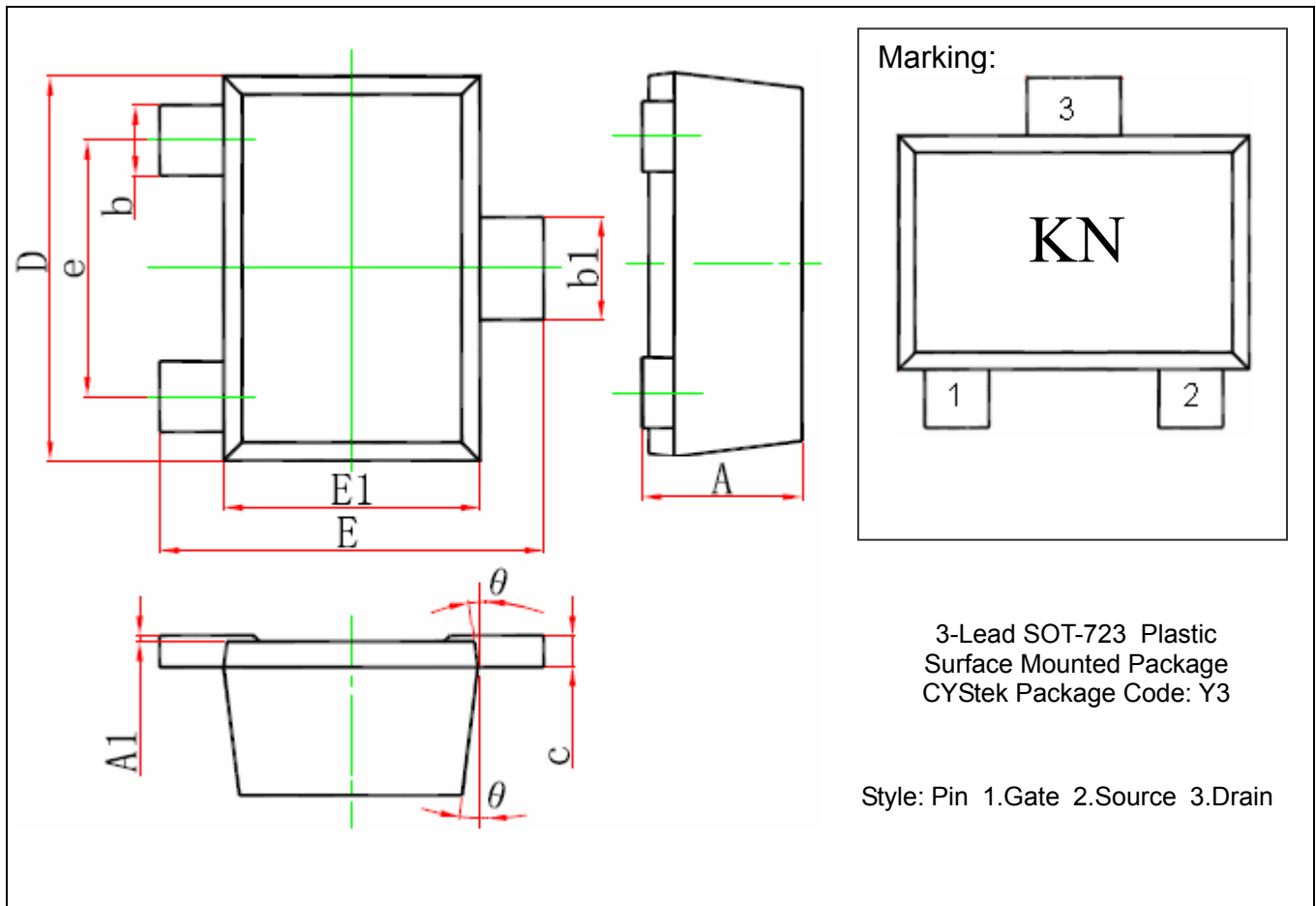
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-723 Dimension**



\*Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.000	0.500	0.000	0.020	D	1.150	1.250	0.045	0.049
A1	0.000	0.050	0.000	0.002	E	1.150	1.250	0.045	0.049
b	0.170	0.270	0.007	0.011	E1	0.750	0.850	0.030	0.033
b1	0.270	0.370	0.011	0.015	e	0.800*		0.031*	
c	0.000	0.150	0.000	0.006	θ	7° REF		7° REF	

- Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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